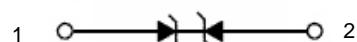


Transient Voltage Suppressors for ESD Protection

General Description

The XESD2FD3V3B is designed to protect voltage sensitive components from ESD and transient voltage events. Excellent clamping capability, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space is at a premium.



SOD882

Applications

- Cellular phones
- Portable devices
- Digital cameras
- Power supplies

Features

- Small Body Outline Dimensions
- Low Body Height
- Peak Power up to 150 Watts @ 8 x 20 μ s Pulse
- Low Leakage current
- Response Time is Typically < 1 ns
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

Ordering information

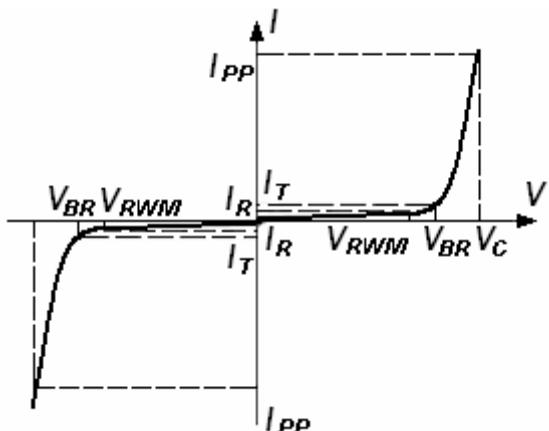
| Device | Marking | Shipping |
|-------------|---------|-----------------|
| XESD2FD3V3B | B | 10000/Tape&Reel |

Absolute Ratings ($T_{amb}=25^{\circ}C$)

| Symbol | Parameter | Value | Units |
|-----------|--|---------------------|-------|
| P_{PP} | Peak Pulse Power ($t_p = 8/20 \mu s$) | 150 | W |
| T_L | Maximum lead temperature for soldering during 10s | 260 | °C |
| T_{stg} | Storage Temperature Range | -55 to +155 | °C |
| T_{op} | Operating Temperature Range | -40 to +125 | °C |
| T_j | Maximum junction temperature | 150 | °C |
| | IEC61000-4-2 (ESD) air discharge contact discharge | ± 15 ± 8 | kV |
| | IEC61000-4-4 (EFT) | 40 | A |
| | ESD Voltage Per Human Body Model | 16 | kV |

Electrical Parameter

| Symbol | Parameter |
|-----------|---|
| I_{PP} | Maximum Reverse Peak Pulse Current |
| V_C | Clamping Voltage @ I_{PP} |
| V_{RWM} | Working Peak Reverse Voltage |
| I_R | Maximum Reverse Leakage Current @ V_{RWM} |
| I_T | Test Current |
| V_{BR} | Breakdown Voltage @ I_T |



Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified. VF = 0.9V at IF = 10mA

| Device | V_{RWM} (V) | I_R (uA) @ V_{RWM} | V_{BR} (V) @ I_T (Note 1) | I_T mA | V_C (V) @ $I_{PP}=5$ A* | V_C (V) @ Max I_{PP}^* | I_{PP} (A)* | P_{PK} (W)* | C (pF) |
|-------------|------------------|---------------------------|----------------------------------|-------------|------------------------------|-------------------------------|------------------|------------------|-----------|
| | Max | Max | Min | | Typ | Max | | | |
| XESD2FD3V3B | 3.3 | 1 | 5.0 | 1.0 | 8.4 | 14.1 | 11.2 | 158 | 25 |

*Surge current waveform per Figure 1.

1. V_{BR} is measured with a pulse test current I_T at an ambient temperature of 25°C.

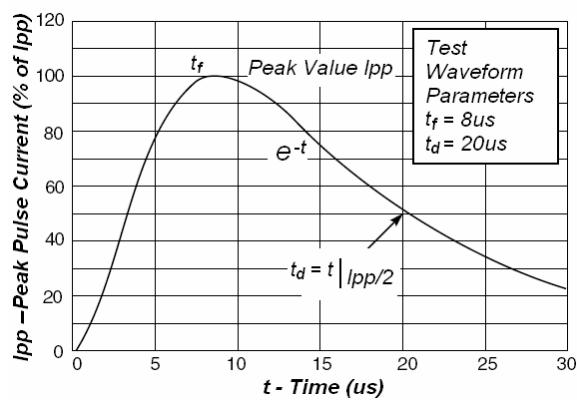


Fig1. Pulse Waveform

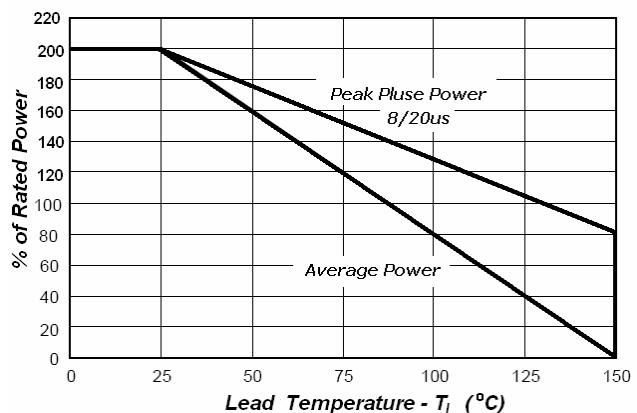


Fig2. Power Derating Curve

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DIMENSION OUTLINE:

Unit:mm

